Supporting Information

Low-temperature and template-free fabrication of cobalt oxide acicular nanotube arrays and their application for supercapacitors

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S1. EIS spectra of the Co₃O₄ ANRAs and Co₃O₄ ANTAs electrodes



Figure S1. EIS spectra of the Co₃O₄ ANRAs and Co₃O₄ ANTAs electrodes, measured in 5.0 M KOH solution at 0.37 V *vs.* Ag/AgCl/KCl (sat'd) with an amplitude of 40 mV. *Inset*: the equivalent circuit, which is composed of the series resistance (R_s), charge-transfer resistance (R_{ct}), and constant phase element (CPE).

S2. Charge-discharge curves of the bare graphite, Co₃O₄ ANRAs and Co₃O₄ ANTAs electrodes at various charge-discharge current densities



Figure S2. Charge-discharge curves of the Co_3O_4 ANTAs electrode measured in 5.0 M KOH solution at various charge-discharge current densities.



Figure S3. Charge-discharge curves of the Co_3O_4 ANRAs electrode measured in 5.0 M KOH solution at various charge-discharge current densities.



Figure S4. Charge-discharge curves of the bare graphite substrate measured in 5.0 M KOH solution at various charge-discharge current densities.

S3. Estimation of the film mass

The 37% HCl solutions containing various concentrations of CoCl₂, with the color ranging from bright blue to transparent, were prepared. The UV-visible spectra of these solutions were measured, and their maximum absorbance at 663 nm was calibrated with the concentration of CoCl₂, as shown in Fig. S5(a). Thereafter, the Co₃O₄ ANRAs and Co₃O₄ ANTAs thin films (3 cm² for each) were dissolved in two batches of 15 mL fresh 37% HCl solution, respectively. The UV-visible spectra of these two solutions were measured, as shown in Fig. S5(b). According to the absorbance at 663 nm shown in Fig. S5(b), the concentrations of Co²⁺ in the solutions of Co₃O₄ ANRAs and Co₃O₄ ANTAs are 0.84 mM and 0.94 mM, respectively. From the molecular weight of Co₃O₄, the masses of the Co₃O₄ ANRAs and Co₃O₄ ANTAs thin films can be estimated to be 0.34 mg/cm² and 0.38 mg/cm², respectively.



Figure S5. (a) Relationship between the absorbance of the $CoCl_2$ solution in 37% HCl at 663 nm and the concentration of $CoCl_2$. (b) UV-visible spectra of the 37% HCl solutions after digesting the Co_3O_4 ANRAs and Co_3O_4 ANTAs thin films.

Morphology of Co ₃ O ₄	Substrate	High-temperature treatment to	Specific capacitance	Reference
		obtain Co_3O_4	(F/g)	
Co ₃ O ₄ nanosheet arrays	Ni foam	\checkmark	2,735	[S1]
Co ₃ O ₄ thin layer	Porous Ni substrate	x	2,200	[S2]
Co ₃ O ₄ nanoflowers	Ni foam	\checkmark	1,937	[S3]
Co ₃ O ₄ nanowires	Carbon fiber paper	\checkmark	1,525	[S4]
Co ₃ O ₄ nanowire arrays	Ni foam	\checkmark	1,257	[S5]
Co ₃ O ₄ nanowire arrays	Ni foam	\checkmark	1,160	[S6]
Co ₃ O ₄ nanonet	Carbon fiber paper	\checkmark	1,124	[S7]
Co ₃ O ₄ nanosheets	Ti foil	×	1,033	[S 8]
Co ₃ O ₄ acicular nanotube arrays	Graphite	×	979	This work
Co ₃ O ₄ nanotubes	Ni foam	\checkmark	574	[S9]
Co ₃ O ₄ microsphere arrays	RGO/CNT paper ^a	×	378	[S10]
Co ₃ O ₄ nanoparticles	Ni foam	\checkmark	363	[S11]
Co ₃ O ₄ hollow-sphere array	Ni foil	\checkmark	358	[S12]
Hollow Co ₃ O ₄ boxes	Ni foam	\checkmark	278	[S13]
Co ₃ O ₄ nanowires	Ni grid	\checkmark	202	[S14]
Hollow Co ₃ O ₄ octahedra	Carbon fiber paper	×	192	[S15]
Porous Co ₃ O ₄	Ni foam	\checkmark	150	[S16]
Co ₃ O ₄ microtubules	Ni foam	\checkmark	131	[S17]
Co ₃ O ₄ nanosheets	Ni grid	\checkmark	92	[S18]

S4. Comparison to the reported studies using Co₃O₄ as pseudocapacitive material

Table S1. Partial list of recent reported studies using Co₃O₄ as pseudocapacitive material.

^a RGO/CNT = Reduced graphene oxide/carbon nanotubes

S5. Charge-discharge curves recorded during 2,000 cycles of measurement



Figure S6. Charge-discharge curve of the Co_3O_4 ANRAs electrode measured in 5.0 M KOH solution at 10 mA/cm², recorded during 2,000 cycles of measurement.



Figure S7. Charge-discharge curve of the Co_3O_4 ANTAs electrode measured in 5.0 M KOH solution at 10 mA/cm², recorded during 2,000 cycles of measurement.

S6. Morphologies of the films after 2,000 cycles of the charge-discharge process



Figure S8. SEM images of the (a) Co_3O_4 ANRAs thin film, and (b) Co_3O_4 ANTAs thin film after 2,000 cycles of the charge-discharge process.

S7. Reference

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